

The present specifications shall apply to Sanken silicon diode, FMB-2204.

回 Type	噺	こゃたつお◎ぬゆ≡ぜ々う◎づ Silicon Schottky Barrier Diode
倭 Structure	却	冕儼嘆傑倭 Resin Molded 嘶嵒kA峒 ^(h) 亶丘 UL94V-0 ト喏囁 Flammability: UL94V-0 (Equivalent)
冂 塾 Applications	咽	偲亶啗勛塶 High Frequency Rectification

No.	項目 Item	符号 Symbol	単位 Unit	規格値 Rating	条件 Conditions
1	ばっか金電圧 Transient Peak Reverse Voltage	V_{RSM}	V	40	
2	ばっか金電圧 Peak Reverse Voltage	V_{RM}	V	40	
3	平均電流 Average Forward Current	$I_{F(AV)}$	A	20	参照 Refer to Derating of 6
4	けいご電流 Peak Surge Forward Current	I_{FSM}	A	150	10msec. 半波 Half sinewave, one shot
5	電流制限値 I_t^2 Limiting Value	I_t^2	A ² s	112	1msec ~ 10msec
6	結晶温度 Junction Temperature	T_j	℃	-40 ~ +150	
7	保存温度 Storage Temperature	T_{stg}	℃	-40 ~ +150	

No.1,2,4&5 show ratings per one chip.

No.	参数名称 Item	符号 Symbol	单位 Unit	数值 Value	测试条件 Conditions
1	正向压降 Forward Voltage Drop	V_F	V	0.55 max.	$I_F=10A$
2	反向漏电流 Reverse Leakage Current	I_R	mA	10 max.	$V_R=V_{RM}$
3	反向漏电流 Reverse Leakage Current Under High Temperature	$H^n I_R$	mA	350 max.	$V_R=V_{RM}, T_j=150^{\circ}C$
4	热阻 Thermal Resistance	$R_{th(j-c)}$	$^{\circ}C/W$	4.0 max.	管壳间 Between Junction and case

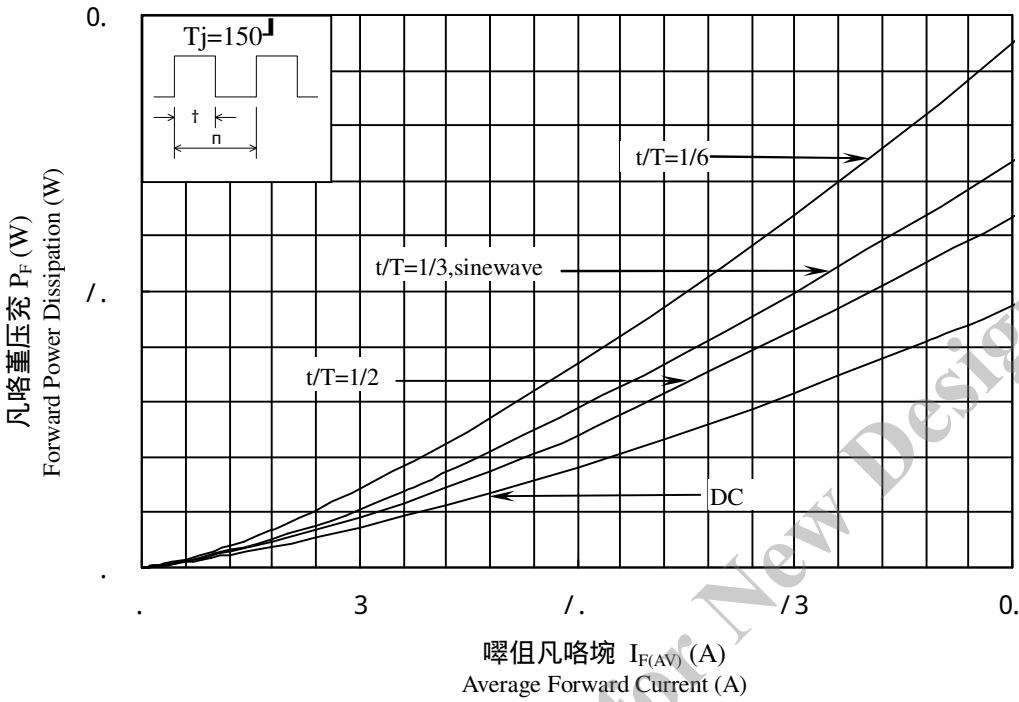
No.1,2,&3 show characteristics per one chip.

⌚ ϕ余勁

Characteristics

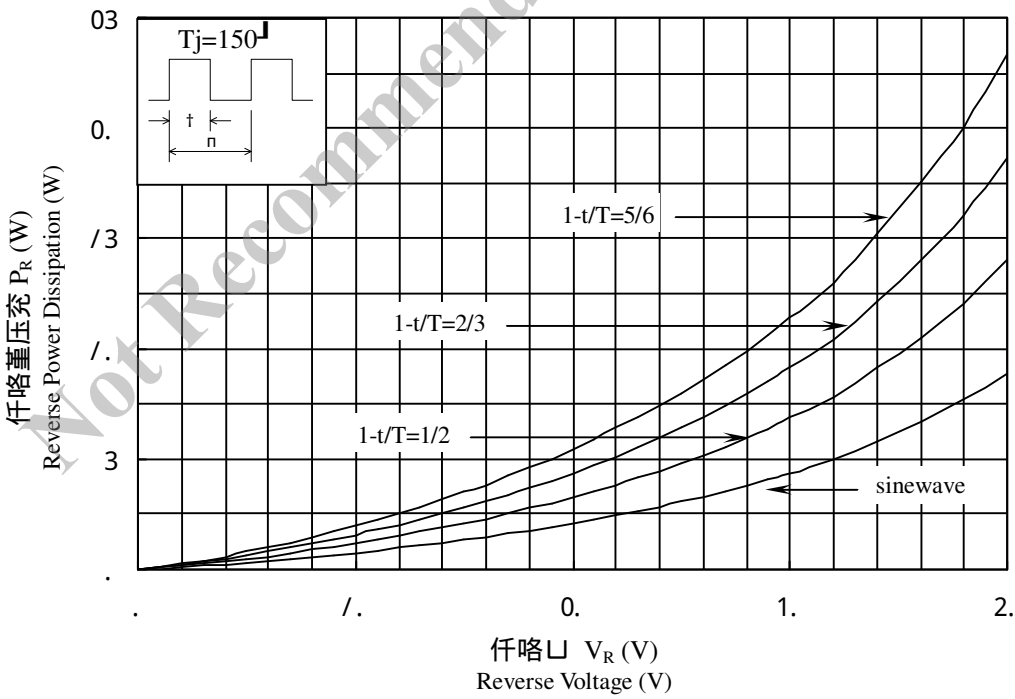
嚟但凡咯塊Ⓢ凡咯董压充

$I_{F(AV)} \rightsquigarrow P_F$

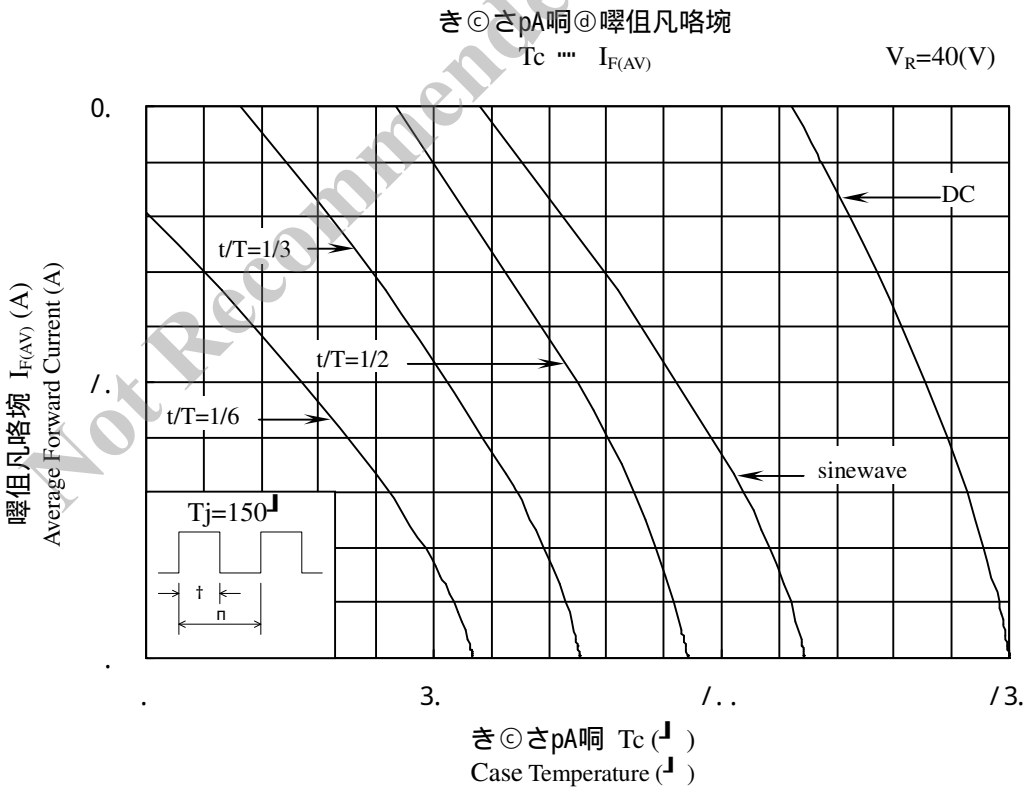
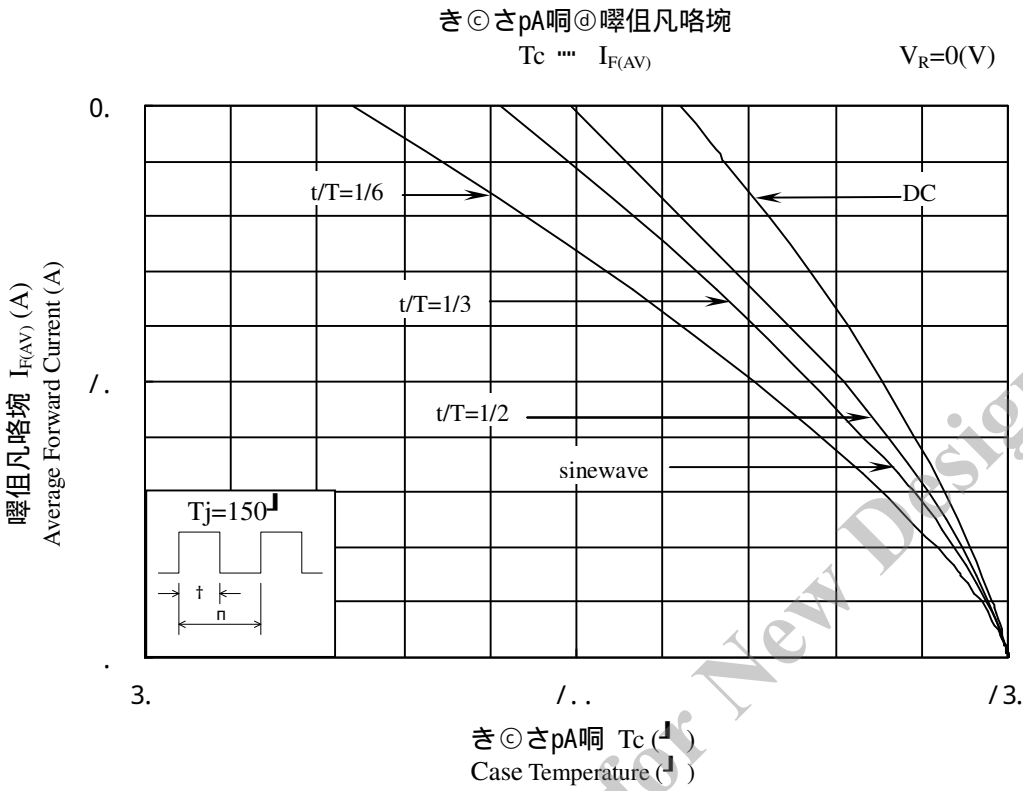


仟咯⌒Ⓢ仟咯董压充

$V_R \rightsquigarrow P_R$



† φ俞嗽丘
Derating



𪛗𪛖𪛖𪛖 Type Name	𪛗𪛖𪛖𪛖𪛖𪛖𪛖𪛖𪛖𪛖𪛖𪛖 Marking		
	𪛗 1𪛖 𪛗场 Type Name	𪛗 2𪛖 世勁 Polarity	𪛗 3𪛖 らたつ鳴傑 Lot number
FMB-2204	B2204		𪛗 1 噸儼 ^(h) 陶(勒垺陶傑mA ^L 佷) 1st letter: Last digit of year 𪛗 2 噸儼 ^(h) 兪𪛖 1 ^h 9 兪 ^L 1 ^h 9 2nd letter: Month𪛖 From 1 to 9 for Jan. to Sep., 10 兪 ^L O(c)11 兪 ^L N(c)12 兪 ^L D O for Oct., N for Nov., D for Dec. 𪛗 3,4 噸儼 ^(h) 啄 3rd & 4th letter: Day 埴 ^(h) 4D20𪛖 (2004 陶 12 兪 20 啄勑却) ex.4D20𪛖 (Dec.20, 2004)